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(54) **ON-CHIP CAPACITORS IN SEMICONDUCTOR DEVICES AND METHODS FOR FORMING THE SAME**

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(57) **ABSTRACT**

A method for forming a three-dimensional (3D) memory device is disclosed. A stack is formed. The stack includes a first region and a second region disposed on a side of the first region along a first direction. The stack includes a first stack in the first region and a second stack in the second region. An interlayer dielectric (ILD) layer is formed over the second stack. Capacitors including first contacts each extending through the ILD layer and disposed on a first side of the second stack along a second direction are formed. The second direction is perpendicular to the first direction.